

Over-voltage Protection Thyristor

Description

DO-214AA P Series solid state protection thyristor protect telecommunications equipment such as modems, line cards, fax machines, and other CPE.

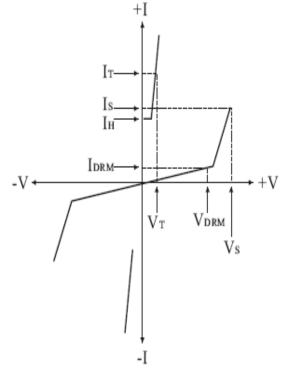
P Series devices are used to enable equipment to meet various regulatory requirements including GR 1089, ITU K.20, K.21 and K.45, IEC 60950, UL 60950, and TIA-968 (formerly known as FCC Part 68).

Compared to surge suppression using other technologies, P Series devices offer absolute surge protection regardless of the surge current available and the rate of applied voltage (dv/dt). P Series devices:

- Cannot be damaged by voltage
- Eliminate hysteresis and heat dissipation typically found with clamping devices
- Eliminate voltage overshoot caused by fast-rising transients
- Are non-degenerative
- Will not fatigu
- Have low capacitance, making them ideal for high-speed transmission equipment

Electrical Parameters

arameter	Definition
C 0	Off-state Capacitance — typical capacitance
	measured in off state
di/dt	Rate of Rise of Current — maximum rated value of
	the acceptable rate of rise in current over time
Is	Switching Current — maximum current required to
	switch to on state
I DRM	Leakage Current — maximum peak off-state current
	measured at VDRM
\mathbf{I}^{H}	Holding Current — minimum current required to
	maintain on state
I PP	Peak Pulse Current — maximum rated peak impulse
	current
\mathbf{I}^{T}	On-state Current — maximum rated continuous
	on-state current
I TSM	Peak One-cycle Surge Current — maximum rated
	one-cycle AC current
Vs	Switching Voltage — maximum voltage prior to
	switching to on state
V DRM	Peak Off-state Voltage — maximum voltage that ca
	be applied while maintaining off state
VF	On-state Forward Voltage — maximum forward
	voltage measured at rated on-state current
VT	On-state Voltage — maximum voltage measured at
	rated on-state current





SP1300SB

P Series

ROHS

Senchip

P Series

ver-voltage Protection Thyristor				SP1300SB				ROHS
ectricalCha	racterist	ics						
Part Number*	Vdrm Volts	Vs Volts	Vr Volts	Idrm µ Amps	Is mAmps	It Amps	In mAmps	Co pF
SP1300SB	120	160	4	5	800	2.2	150	40

* For surge ratings, see table below.

Notes:

• All measurements are made at an ambient temperature of 25°C. IPP applies to -40°C through +85°C temperature range.

• Off-state capacitance (Co) is measured at 1 MHz with a 2 V bias and is typical value.

Series	Ipp 2/10 μs Amps	IPP 8/20 µs Amps	Ipp 10/160 µs Amps	Ipp 10/560 µs Amps	Ipp 10/1000 µs Amps	Itsm 60 Hz Amps	di/dt Amps∕µs
В	250	250	150	100	80	30	500

Package DO-214AA/SMB	Symbol	Parameter	Value	Unit
	$T_{\rm J}$	Operating Junction Temperature	-40 to +150	°C
	Ts	Storage Temperature Range	-40 to +150	°C
	$R_{\theta \ JA}$	Junction to Ambient on printed circuit	90	°C/W



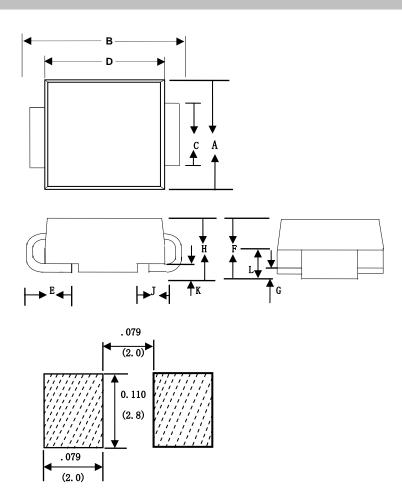
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Dimensions



SMB

Dimension	In	ches	Millimeters		
Dimension	MIN	MAX	MIN	MAX	
А	0.134	0. 155	3. 40	3.94	
В	0. 205	0.22	5. 21	5. 59	
С	0.075	0. 083	1.90	2.11	
D	0.166	0. 185	4. 22	4. 70	
E	0.036	0.056	0. 91	1.42	
F	0.073	0. 087	1.85	2.2	
G	0.002	0.008	0. 05	0. 20	
Н	0.077	0.094	1.95	2.40	
J	0. 043	0. 053	1.09	1.35	
K	0.008	0.014	0. 20	0.35	
L	0. 039	0. 049	0. 99	1.24	

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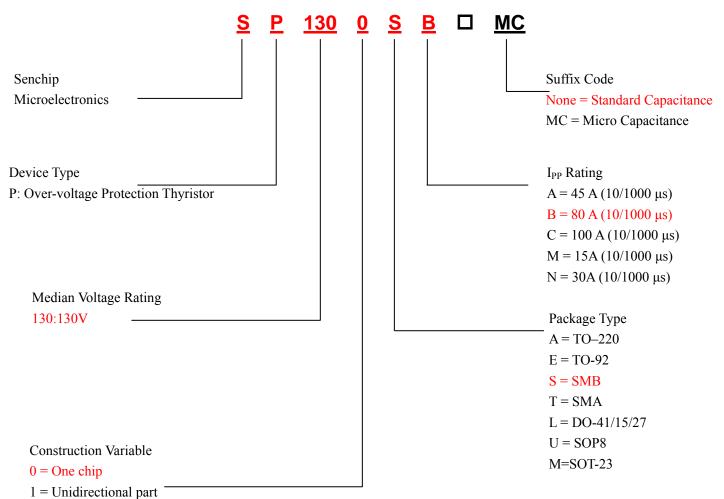
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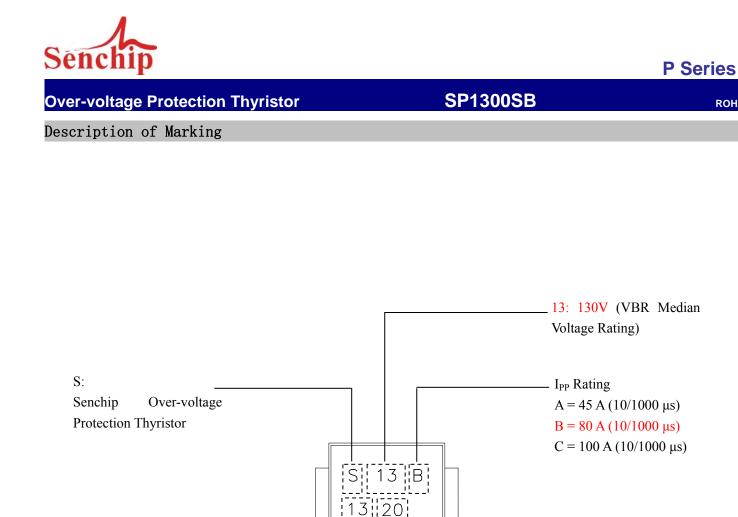
SP1300SB

ROHS

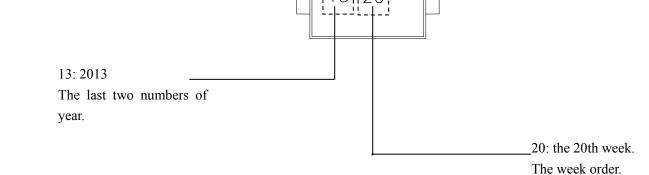
Description of Part Number



- 2 = Two chips
- 2 1 we chips
- 3 = Three chips



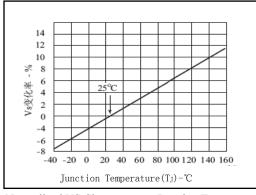
ROHS





Senchip	P Series		
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Summary of Packing	Options		
Package Type	Description	Packing Quantity	Industry Standard
DO-214AA SMB			
	Embossed Carrier Reel Pack	2500 PCS	EIA RS-481

Thermal Derating Curves



Normalized VS Change versus Junction Temperature

